In the Claims:

Please cancel claims 1-20, and append new claims 21-26 as follows:

21. (new) A method of achieving a resonant frequency of acoustic resonators comprising:

fabricating a plurality of said acoustic resonators on a basis of forming each said acoustic resonator to include an electrode-piezoelectric stack in which layer dimensions are selected to achieve an intended operational resonant frequency, said intended operational resonant frequency being a target final operational resonant frequency, each said electrode-piezoelectric stack having conductive electrode layers;

determining whether said acoustic resonators have current resonant frequencies that are within an acceptable margin of error of said intended operational resonant frequency; and

for occasions in which said current resonant frequencies are outside of said acceptable margin of error, exposing said acoustic resonators to a controlled gaseous environment in which at least one said electrode layer is oxidized, including intentionally regulating said controlled gaseous environment on a basis of providing each said acoustic resonator with a final operational resonant frequency that is within said margin of error of said intended operational resonant frequency.

22. (new) The method of claim 21 wherein said exposing includes controlling temperature and controlling oxygen content within said controlled gaseous environment based on establishing said final operational resonant frequencies within said margin of error of said intended operational resonant frequency.

23. (new) The method of claim 21 wherein said exposing includes regulating said temperature and oxygen content to provide a downward adjustment of said resonant frequencies in a controlled manner.

24. (new) The method of claim 23 wherein said exposing further includes controlling flow rates of gases, including oxygen.

25. (new) The method of claim 24 wherein said exposing occurs within a Rapid Thermal Annealer (RTA).

26. (new) The method of claim 21 wherein said exposing occurs at a temperature not exceeding 215°C.

COMPLETE LISTING OF CLAIMS IN THE PATENT APPLICATION

1-20. Cancelled.

21. (new) A method of achieving a resonant frequency of acoustic resonators comprising:

fabricating a plurality of said acoustic resonators on a basis of forming each said acoustic resonator to include an electrode-piezoelectric stack in which layer dimensions are selected to achieve an intended operational resonant frequency, said intended operational resonant frequency being a target final operational resonant frequency, each said electrode-piezoelectric stack having conductive electrode layers;

determining whether said acoustic resonators have current resonant frequencies that are within an acceptable margin of error of said intended operational resonant frequency; and

for occasions in which said current resonant frequencies are outside of said acceptable margin of error, exposing said acoustic resonators to a controlled gaseous environment in which at least one said electrode layer is oxidized, including intentionally regulating said controlled gaseous environment on a basis of providing each said acoustic resonator with a final operational resonant frequency that is within said margin of error of said intended operational resonant frequency.

22. (new) The method of claim 21 wherein said exposing includes controlling temperature and controlling oxygen content within said controlled gaseous environment based on establishing said final operational resonant frequencies within said margin of error of said intended operational resonant frequency.

23. (new) The method of claim 21 wherein said exposing includes regulating said temperature and oxygen content to provide a downward adjustment of said resonant frequencies in a controlled manner.

24. (new) The method of claim 23 wherein said exposing further includes controlling flow rates of gases, including oxygen.

25. (new) The method of claim 24 wherein said exposing occurs within a Rapid Thermal Annealer (RTA).

26. (new) The method of claim 21 wherein said exposing occurs at a temperature not exceeding 215°C.